HALOGEN

FREE



Hyper Fast Rectifier, 2 x 3 A FRED Pt[®]



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PRODUCT SUMMARY							
Package	FlatPAK 5 x 6						
I _{F(AV)}	2 x 3 A						
V _R	200 V						
V _F at I _F	0.71 V						
t _{rr}	25 ns						
T _J max.	175 °C						
Diode variation	Separated cathode						

FEATURES

- Hyper fast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature COMPLIANT
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant M3 suffix meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200				
Average rectified forward current per de		T _{Solderpad} = 170 °C, DC	3	V			
Average rectilied forward current per de	VICE I _{F(AV)}	T _{Solderpad} = 169 °C, D = 0.5	5				
Non-repetitive peak surge current		$T_J = 25 \ ^{\circ}C$, 10 ms sinusoidal pulse	147	А			
per d	iode I _{FSM}		70	~			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward voltage	V _F	I _F = 3 A	-	0.88	0.94	V		
Forward voltage		I _F = 3 A, T _J = 150 °C	-	0.71	0.74]		
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	2			
neverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	6	40	μA		
Junction capacitance	CT	V _R = 200 V	-	14	-	pF		

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/µs, V _R = 30 V	-	26	-		
	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25	20	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	15	-	ns	
		T _J = 125 °C	I _F = 3 A dI _F /dt = 200 A/μs V _R = 160 V	-	25	-		
Deals receiver sourcent	1	T _J = 25 °C		-	2	-	٨	
Peak recovery current	IRRM	T _J = 125 °C		-	3	-	A	
	0	T _J = 25 °C		-	12	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	40	-	ПС	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	90	103			
Thermal resistance, junction to case	R _{thJC} ⁽³⁾		-	2.3	2.6	°C/W		

Notes

- ⁽¹⁾ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1 \times R_{thJA}$
- ⁽²⁾ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} junction to ambient

⁽³⁾ Mounted on infinite heatsink

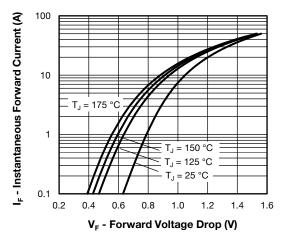


Fig. 1 - Typical Forward Voltage Drop Characteristics

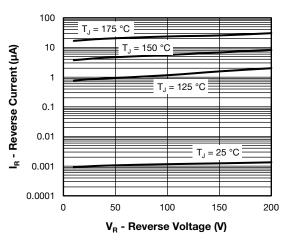


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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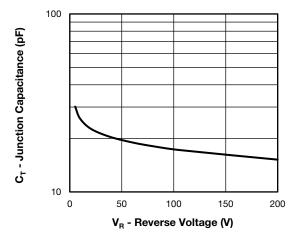


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

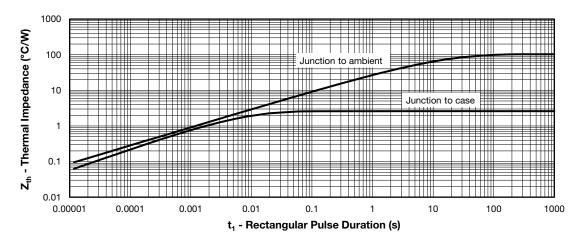
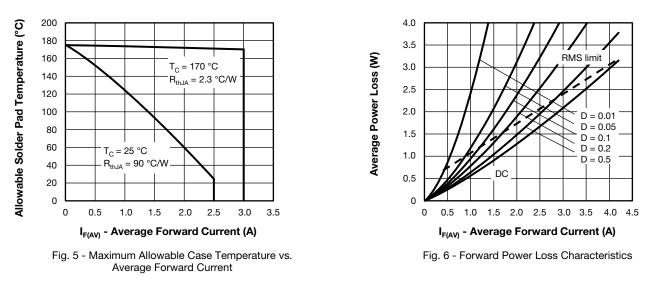


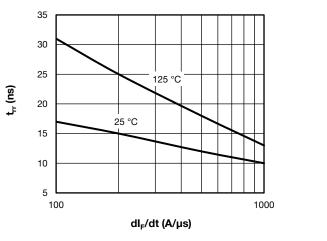
Fig. 4 - Maximum Thermal Impedance Zth Characteristics



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Fig. 7 - Typical Reverse Recovery vs. dl_F/dt



⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{Fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

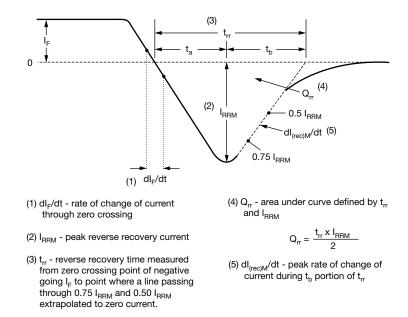
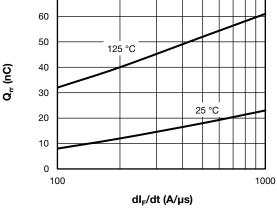


Fig. 9 - Reverse Recovery Waveform and Definitions



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Fig. 8 - Typical Stored Charge vs. dl_F/dt



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ORDERING INFORMATION TABLE

Device code	vs-	6	D	к	н	02	-МЗ
		2	3	4	5	6	7
	1	- Vis	hay Sen	nicondu	ctors pro	oduct	
	2	- Cur	rent rati	ng (6 =	6 A)		
	3	- Circ	cuit conf	iguratio	า:		
		D =	separat	ed cath	ode		
	4	- K=	FlatPA	<pre>< packa</pre>	ge		
	5	- Pro	cess typ	e:			
		H =	hyperfa	st recov	/ery		
	6	- Vol	tage coo	le (02 =	200 V)		
	7	M3	8 = halog	gen-free	, RoHS-	complia	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N UNIT WEIGHT (g) PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPT							
VS-6DKH02-M3/H	0.10	н	1500	7"diameter plastic tape and reel			
VS-6DKH02-M3/I	0.10	l	6000	13"diameter plastic tape and reel			

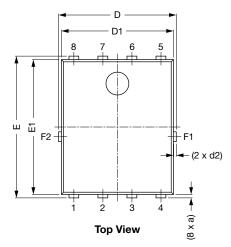
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96056					
Part marking information	www.vishay.com/doc?96059				
Packaging information	www.vishay.com/doc?88869				

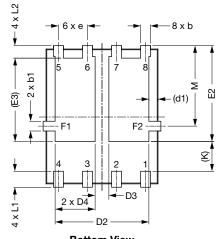




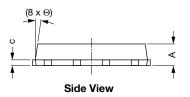
FlatPAK 5 x 6 (Dual)

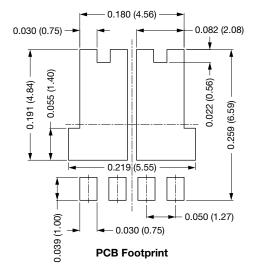
DIMENSIONS in inches (millimeters)











DIM		INCHES			MILLIMETERS	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.035	0.039	0.043	0.89	0.99	1.09
(a)	-	0.006	-	-	0.15	-
b	0.013	0.017	0.020	0.32	0.43	0.52
b1	0.013	0.017	0.020	0.32	0.43	0.52
С	0.008	-	0.014	0.20	-	0.35
D	0.197	0.203	0.209	5.00	5.15	5.30
D1	0.189	0.193	0.197	4.80	4.90	5.00
D2	0.154	0.161	0.169	3.90	4.10	4.30
D3	0.020	0.024	0.031	0.50	0.60	0.80
D4	0.063	0.069	0.075	1.60	1.75	1.90
(d1)	-	0.016	-	-	0.40	-
(d2)	-	0.005	-	-	0.125	-
E	0.238	0.244	0.250	6.05	6.20	6.35

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Outline Dimensions



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DIM.		INCHES		MILLIMETERS				
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	-	-	3.65	-		
е		0.050 BSC		1.27 BSC				
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
М	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

Notes

٠ Dimensioning and tolerancing per ASME Y14.5-2009

Dimensions D1 and E1 do not include mold flash or gate burrs ٠

Dimension (XX) means reference only ٠



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